

**Vishay Siliconix** 

# Low-Voltage Single SPDT MICRO FOOT<sup>®</sup> Analog Switch

## DESCRIPTION

The DG3000 is a single-pole/double-throw monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low power, high speed (t<sub>ON</sub>: 24 ns, t<sub>OFF</sub>: 9 ns), low on-resistance (r<sub>DS(on)</sub>: 1.4  $\Omega$ ) and small physical size (MICRO FOOT, 6-bump), the DG3000 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG3000 is built on Vishay Siliconix's low voltage JI2 process. An epitaxial layer prevents latchup. Break-before - make is guaranteed for DG3000.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. For MICRO FOOT analog switching products manufactured with tin/ silver/copper (Sn/Ag/Cu) device terminations, the lead (Pb)-free "-E1" suffix is being used as a designator.

#### FEATURES

- MICRO FOOT<sup>®</sup> Chip Scale Package (1.07 x 1.57 mm)
- Low Voltage Operation (1.8 V to 5.5 V)
- Low On-Resistance  $r_{DS(on)}$ : 1.4  $\Omega$
- Fast Switching t<sub>ON</sub>: 24 ns, t<sub>OFF</sub>: 9 ns
- Low Power Consumption
- TTL/CMOS Compatible

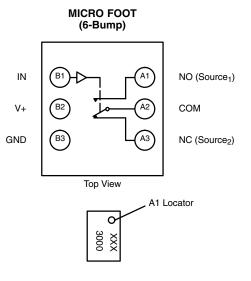
#### BENEFITS

- Reduced Power Consumption
- Simple Logic Interface
- High Accuracy
- Reduce Board Space

#### **APPLICATIONS**

- Cellular Phones
- Communication Systems
- Portable Test Equipment
- · Battery Operated Systems
- PCM Cards
- PDA

#### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



**Device Marking:** 3000 xxx = Date/Lot Traceability Code

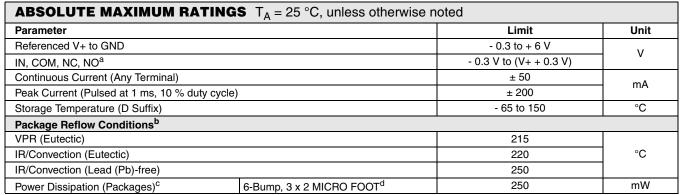
TRUTH TABLE						
Logic	NC	NO				
0	ON	OFF				
1	OFF	ON				

ORDERING INFORMATION						
Temp Range	Package	Part Number				
- 40 to 85 °C	MICRO FOOT: 6-Bump 3 x 2, 0.5 mm Pitch 165 µm nom. bump height (Eutectic, SnPb)	DG3000DB-T1				
	MICRO FOOT: 6-Bump 3 x 2, 0.5 mm pitch, 238 µm nom. bump height (Lead (Pb)-free, Sn/Ag/Cu)	DG3000DB-T1-E1				

\* Pb containing terminations are not RoHS compliant, exemptions may apply.



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Notes:

a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. Refer to IPC/JEDEC (J-STD-020A). No hand/manual solder rework recommended.

c. All bumps soldered to PC Board.

d. Derate 3.1 mW/°C above 70 °C.

SPECIFICATIONS (V+ = 2.0 V)							
		Test Conditions Otherwise Unless Specified		Limits - 40 to 85 °C			
Parameter	Symbol	V+ = 2.0 V, $\pm$ 10 %, V <sub>IN</sub> = 0.4 or 1.6 V <sup>e</sup>	Temp <sup>a</sup>	Min <sup>b</sup>	Тур <sup>с</sup>	Max <sup>b</sup>	Unit
Analog Switch							
Analog Signal Range <sup>d</sup>	$V_{ m NO}^{}, V_{ m NC}^{}$ $V_{ m COM}^{}$		Full	0		V+	v
On-Resistance	r <sub>ON</sub>	V+ = 1.8 V, V <sub>COM</sub> = 1.0 V, I <sub>NO</sub> , I <sub>NC</sub> = 10 mA	Room Full <sup>d</sup>		17	20 22.5	Ω
r <sub>ON</sub> Flatness <sup>d</sup>	r <sub>ON</sub> Flatness	V+ = 1.8 V, V <sub>COM</sub> = 0 to V+, I <sub>NO</sub> , I <sub>NC</sub> = 10 mA	Room		14		52
Switch Off Leakage Current <sup>f</sup>	I <sub>NO(off)</sub> I <sub>NC(off)</sub>	V+ = 2.2 V	Room Full <sup>d</sup>	- 700 - 11		700 11	pA nA
Switch On Leakage Current	I <sub>COM(off)</sub>	$V_{NO}, V_{NC} = 0.5 \text{ V/1.5 V}, V_{COM} = 1.5 \text{ V/0.5 V}$	Room Full <sup>d</sup>	- 700 - 11		700 11	pA nA
Channel-On Leakage Current <sup>f</sup>	I <sub>COM(on)</sub>	V+ = 2.2 V, V <sub>NO</sub> , V <sub>NC</sub> = V <sub>COM</sub> = 0.5 V/1.5 V	Room Full <sup>d</sup>	- 700 - 11		700 11	pA nA
Digital Control							
Input High Voltage	V <sub>INH</sub>		Full	1.6			v
Input Low Voltage	V <sub>INL</sub>		Full			0.4	-
Input Capacitance <sup>d</sup>	C <sub>in</sub>		Full		5		pF
Input Current <sup>d</sup>	I <sub>INL</sub> or I <sub>INH</sub>	$V_{IN} = 0 \text{ or } V+$	Full	- 1		1	μA
Dynamic Characteristics					1		1
Turn-On Time	t <sub>ON</sub>		Room Full <sup>d</sup>		61	76 79	
Turn-Off Time	t <sub>OFF</sub>	$V_{NO} \text{ or } V_{NC}$ = 1.5 V, $R_L$ = 300 $\Omega,  C_L$ = 35 pF Figures 1 and 2	Room Full <sup>d</sup>		17	33 36	ns
Break-Before-Make Time	t <sub>d</sub>		Room	1	45		
Charge Injection <sup>d</sup>	Q <sub>INJ</sub>	$C_L$ = 1 nF, $V_{GEN}$ = 0 V, $R_{GEN}$ = 0 $\Omega$ , Figure 3	Room		2		рС
Off-Isolation <sup>d</sup>	OIRR	$R_1 = 50 \Omega, C_1 = 5 pF, f = 1 MHz$	Room		- 61		dB
Crosstalk <sup>d</sup>	X <sub>TALK</sub>		Room		- 67		uр
NO, NC Off Capacitance <sup>d</sup>	$\begin{array}{c} C_{NO(off)} \\ C_{NC(off)} \end{array}$	V <sub>IN</sub> = 0 or V+, f = 1 MHz			31		pF
Channel-On Capacitance <sup>d</sup>	C <sub>ON</sub>		Room		98		
Power Supply							
Power Supply Range	V+			1.8		2.2	V
Power Supply Current <sup>d</sup>	l+	V <sub>IN</sub> = 0 or V+			0.1	1.0	μA
Power Consumption	P <sub>C</sub>	v <sub>IN</sub> = 0 01 v+				2.2	μW



Parameter	Symbol	Test Conditions Otherwise Unless Specified	Temp <sup>a</sup>	Limits - 40 to 85 °C			Unit
	-	V+ = 3 V, $\pm$ 10 %, V <sub>IN</sub> = 0.4 or 2.0 V <sup>e</sup>		Min <sup>b</sup>	Тур <sup>с</sup>	Max <sup>b</sup>	
Analog Switch							
Analog Signal Range <sup>d</sup>	V <sub>NO</sub> , V <sub>NC</sub> V <sub>COM</sub>		Full	0		V+	v
On-Resistance <sup>d</sup>	r <sub>ON</sub>	V+ = 2.7 V, V <sub>COM</sub> = 1.5 V, I <sub>NO</sub> , I <sub>NC</sub> = 10 mA	Room Full		3.3 3.4	4.1 4.2	0
r <sub>ON</sub> Flatness <sup>d</sup>	r <sub>ON</sub> Flatness	V+ = 2.7 V, V <sub>COM</sub> = 0 to V+, I <sub>NO</sub> , I <sub>NC</sub> = 10 mA	Room		1.3		Ω
Switch Off Leakage Current <sup>f</sup>	I <sub>NO(off)</sub> I <sub>NC(off)</sub>	V+ = 3.3 V	Room Full	- 800 - 13		800 13	pA nA
Switch On Leakage Current	I <sub>COM(off)</sub>	$V_{NO}$ , $V_{NC}$ = 1 V/3 V, $V_{COM}$ = 3 V/1 V	Room Full	- 800 - 13		800 13	pA nA
Channel-On Leakage Current <sup>f</sup>	I <sub>COM(on)</sub>	V+ = 3.3 V, V <sub>NO</sub> , V <sub>NC</sub> = V <sub>COM</sub> = 1 V/3 V	Room Full	- 800 - 13		800 13	pA nA
Digital Control							
Input High Voltage	V <sub>INH</sub>			2			v
Input Low Voltage	V <sub>INL</sub>		Full			0.4	1 <sup>v</sup>
Input Capacitance <sup>d</sup>	C <sub>in</sub>		Full		5		pF
Input Current <sup>d</sup>	$I_{\rm INL}$ or $I_{\rm INH}$	V <sub>IN</sub> = 0 or V+	Full	- 1		1	μA
Dynamic Characteristics							
Turn-On Time <sup>d</sup>	t <sub>ON</sub>	$V_{NO}$ or $V_{NC}$ = 2.0 V, $R_L$ = 300 $\Omega$ , $C_L$ = 35 pF	Room Full		34	49 52	
Turn-Off Time <sup>d</sup>	t <sub>OFF</sub>	Figures 1 and 2	Room Full		12	30 33	ns
Break-Before-Make Time <sup>d</sup>	t <sub>d</sub>		Room	1	23		
Charge Injection <sup>d</sup>	Q <sub>INJ</sub>	$C_L$ = 1 nF, $V_{GEN}$ = 0 V, $R_{GEN}$ = 0 $\Omega$ , Figure 3	Room		4		pC
Off-Isolation <sup>d</sup>	OIRR	R <sub>1</sub> = 50 Ω, C <sub>1</sub> = 5 pF, f = 1 MHz	Room		- 61		- dB
Crosstalk <sup>d</sup>	X <sub>TALK</sub>	$H_{L} = 50.52, O_{L} = 5 \text{ pr}, T = 1 \text{ Minz}$	Room		- 67		uБ
NO, NC Off Capacitance <sup>d</sup>	C <sub>NO(off)</sub> C <sub>NC(off)</sub>	V <sub>IN</sub> = 0 or V+, f = 1 MHz	Room		31		pF
Channel-On Capacitance <sup>d</sup>	C <sub>ON</sub>	Room			47		]
Power Supply							
Power Supply Range	V+			2.7		3.3	V
Power Supply Current <sup>d</sup>	l+	V <sub>IN</sub> = 0 or V+			0.1	1.0	μA
Power Consumption	P <sub>C</sub>					3.3	μW

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SPECIFICATIONS (V+ = 5.0 V)								
Parameter	Symbol	Test Conditions Otherwise Unless Specified	Temp <sup>a</sup>	<b>Limits</b> - 40 to 85 °C			Unit	
	- <b>,</b>	V+ = 5 V, $\pm$ 10 %, V <sub>IN</sub> = 0.8 or 2.4 V <sup>e</sup>	Temp	Min <sup>b</sup>	Тур <sup>с</sup>	Max <sup>b</sup>		
Analog Switch								
Analog Signal Range <sup>d</sup>	V <sub>NO</sub> , V <sub>NC</sub> V <sub>COM</sub>		Full	0		V+	v	
On- Resistance	r <sub>ON</sub>	V+ = 4.5 V, V <sub>COM</sub> = 3 V, I <sub>NO</sub> , I <sub>NC</sub> = 10 mA	Room Full		1.4 1.6	2.3 2.8	Ω	
r <sub>ON</sub> Flatness <sup>d</sup>	r <sub>ON</sub> Flatness	V+ = 4.5 V, V <sub>COM</sub> = 0 to V+, I <sub>NO</sub> , I <sub>NC</sub> = 10 mA	Room		0.5		52	
Switch Off Leakage Current	I <sub>NO(off)</sub> I <sub>NC(off)</sub>	V+ = 5.5 V	Room Full	- 1.2 - 21		1.2 21		
Switch On Ecakage Guitent	I <sub>COM(off)</sub>	$V_{NO}$ , $V_{NC}$ = 1 V/4.5 V, $V_{COM}$ = 4.5 V/1 V	Room Full	- 1.2 - 21		1.2 21	nA	
Channel-On Leakage Current	I <sub>COM(on)</sub>	V+ = 5.5 V, V+ = 5.5 V V <sub>NO</sub> , V <sub>NC</sub> = V <sub>COM</sub> = 1 V/4.5 V	Room Full	- 1.2 - 21		1.2 21		
Digital Control			•					
Input High Voltage	V <sub>INH</sub>		Full	2.4			v	
Input Low Voltage	V <sub>INL</sub>		Full			0.8	v	
Input Capacitance	C <sub>in</sub>		Full		5		pF	
Input Current	I <sub>INL</sub> or I <sub>INH</sub>	V <sub>IN</sub> = 0 or V+	Full	- 1		1	μA	
Dynamic Characteristics								
Turn-On Time <sup>d</sup>	t <sub>ON</sub>	$V_{NO}$ or $V_{NC}$ = 3 V, $R_L$ = 300 $\Omega$ , $C_L$ = 35 pF	Room Full		24	36 39		
Turn-Off Time <sup>d</sup>	t <sub>OFF</sub>	$v_{NO}$ of $v_{NC} = 3$ v, $H_L = 300$ 32, $C_L = 35$ pF Figures 1 and 2	Room Full		9	22 25	ns	
Break-Before-Make Time <sup>d</sup>	t <sub>d</sub>		Room	1	15			
Charge Injection <sup>d</sup>	Q <sub>INJ</sub>	$C_L$ = 1 nF, $V_{GEN}$ = 0 V, $R_{GEN}$ = 0 $\Omega$ , Figure 3	Room		38		pC	
Off-Isolation <sup>d</sup>	OIRR	$R_1 = 50 \Omega_2 C_1 = 5 pF_2 f = 1 MHz$	Room		- 61		dB	
Crosstalk <sup>d</sup>	X <sub>TALK</sub>	$r_1 = 30.32$ , $O_1 = 3.40$ , $r = 1.100.02$	Room		- 67		uБ	
Source-Off Capacitance <sup>d</sup>	C <sub>NO(off)</sub> C <sub>NC(off)</sub>	V <sub>IN</sub> = 0 or V+, f = 1 MHz Room			30		pF	
Channel-On Capacitance <sup>d</sup>	C <sub>ON</sub>				96		1	
Power Supply								
Power Supply Range	V+			4.5		5.5	V	
Power Supply Current	l+	V <sub>IN</sub> = 0 or V+			0.1	1.0	μA	
Power Consumption	Power Consumption $P_C$					5.5	μW	

Notes:

a. Room = 25 °C, Full = as determined by the operating suffix.

b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

c. Typical values are for design aid only, not guaranteed nor subject to production testing.

d. Guarantee by design, nor subjected to production test.

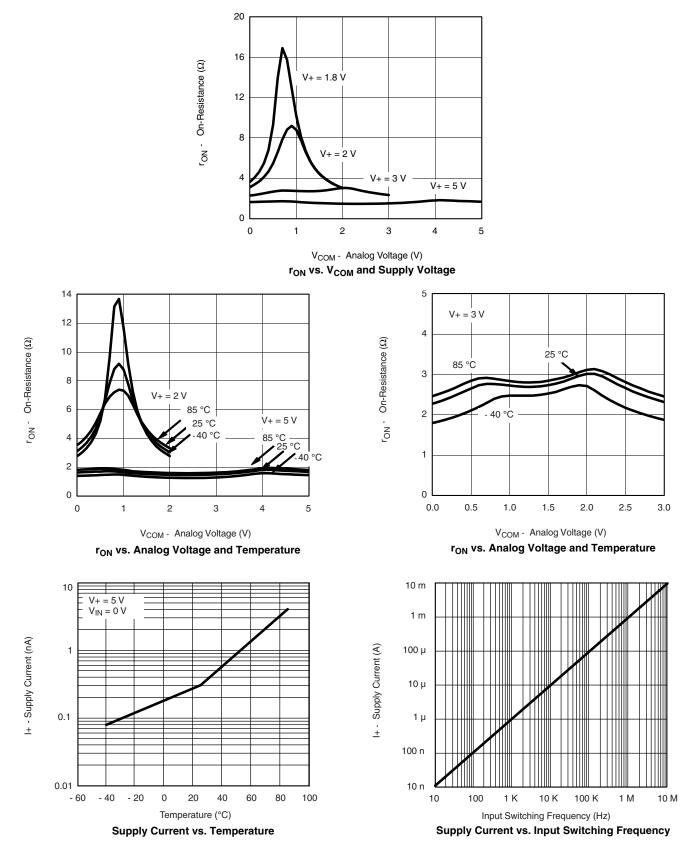
e. V<sub>IN</sub> = input voltage to perform proper function.

f. Guaranteed by 5 V leakage testing, not production tested.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

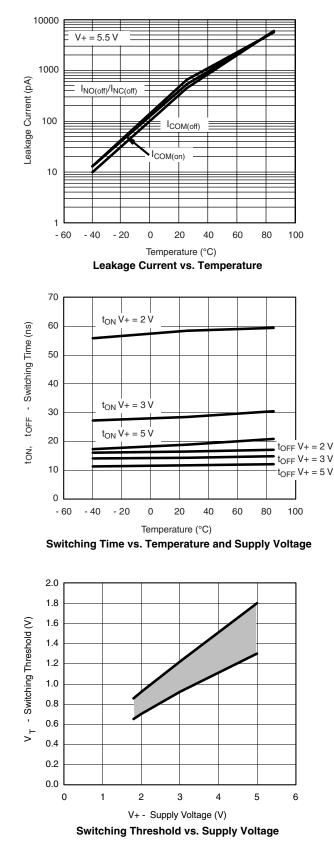


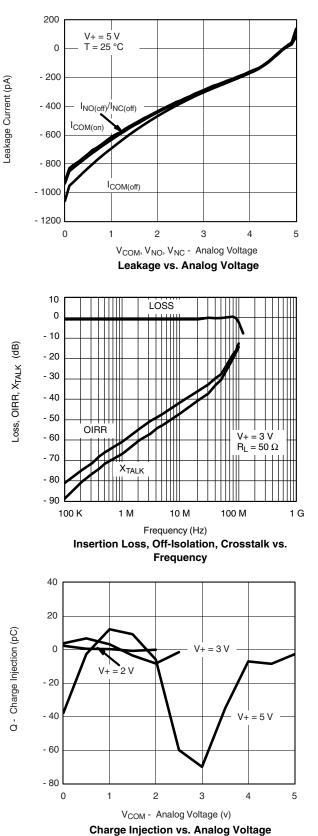
Document Number: 71742 S-70853–Rev. F, 30-Apr-07



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## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





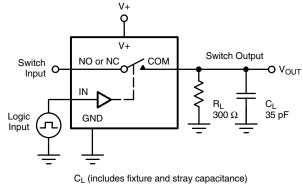
## **DG3000** Vishay Siliconix

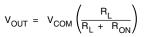
t<sub>r</sub> < 5 ns

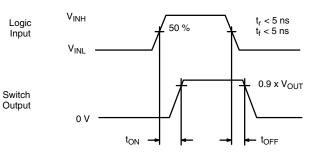
t<sub>f</sub> < 5 ns

t<sub>D</sub>

## **TEST CIRCUITS**







Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.



 $V_{\text{INH}}$ 

 $V_{\text{INL}}$ 

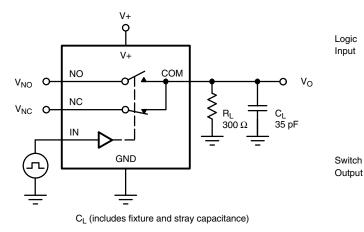
Vo

0 V

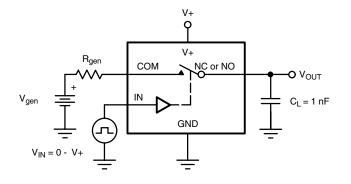
90 %

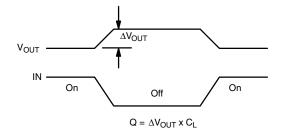
t<sub>D</sub>

 $V_{NC} = V_{NO}$ 









IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection



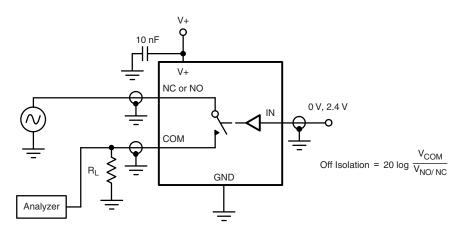
VISHAY

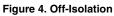
# DG3000

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## **TEST CIRCUITS**





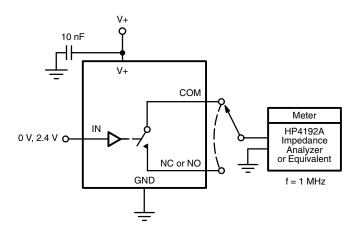
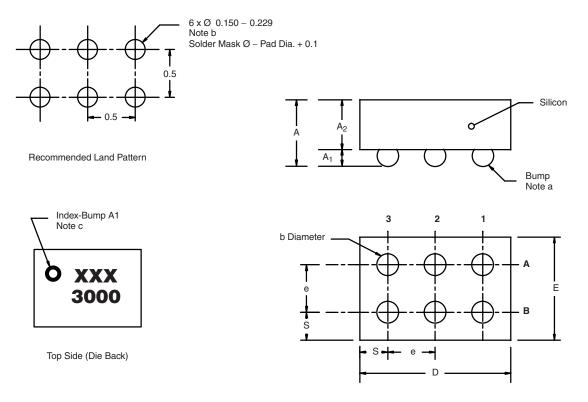


Figure 5. Channel Off/On Capacitance



## **PACKAGE OUTLINE**

## MICRO FOOT: 6-BUMP (3 x 2, 0.5 mm PITCH)



Notes (Unless Otherwise Specified):

a. Bump is Eutectic 63/57 Sn/Pb or Lead (Pb)-free Sn/Ag/Cu.

b. Non-solder mask defined copper landing pad.

c. Laser Mark on silicon die back; no coating. Shown is not actual marking; sample only.

EUTECTIC (Sn/Pb)					
	Millim	eters <sup>a</sup>	Inches		
Dim	Min	Max	Min	Max	
Α	0.615	0.715	0.0242	0.0281	
A <sub>1</sub>	0.140	0.190	0.0055	0.0075	
A <sub>2</sub>	0.470	0.495	0.0185	0.0195	
b	0.180	0.250	0.0071	0.0098	
D	1.555	1.585	0.0612	0.0624	
E	1.055	1.085	0.0415	0.0427	
е	0.5 B	ASIC	0.0197 BASIC		
S	0.278	0.293	0.0109	0.0115	
Matea					

LEAD (Pb)-FREE (Sn/Ag/Cu)					
	Millim	eters <sup>a</sup>	Inches		
Dim	Min	Max	Min	Max	
Α	0.688	0.753	0.0271	0.0296	
<b>A</b> <sub>1</sub>	0.218	0.258	0.0086	0.0102	
A <sub>2</sub>	0.470	0.495	0.0185	0.0195	
b	0.306	0.346	0.0120	0.0136	
D	1.555	1.585	0.0612	0.0624	
E	1.055	1.085	0.0415	0.0427	
е	0.5 BASIC 0.0197 BASIC			BASIC	
S	0.278	0.293	0.0109	0.0115	

Notes:

a. Use millimeters as the primary measurement.

Notes:

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Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?71742.



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